

Bernd Aichner,^{1,*} Sandra Keppert,^{2,*} Johannes D. Pedarnig,² and Wolfgang Lang^{1,†}

¹Faculty of Physics, University of Vienna, Boltzmanngasse 5, 1090 Vienna, Austria

²Institute of Applied Physics, Johannes Kepler University Linz, Altenberger Strasse 69, 4040 Linz, Austria

(Dated: December 24, 2024)

Few-unit cell thick $Bi_2Sr_2CaCu_2O_{8+\delta}$ (Bi-2212) layers have recently attracted much interest due to their extreme anisotropy and two-dimensional superconductivity, although they are typically susceptible to ambient conditions. In this study, we report on thin films approximately 13 unit cells thick that are stable in air, exhibit high anisotropy, and demonstrate extraordinarily high critical currents. By examining the superconducting transition under magnetic fields applied in both outof-plane and in-plane orientations, we estimate key parameters such as pinning potentials, coherence lengths, London penetration depth, anisotropy factor, and the Ginzburg-Landau parameter. The volume pinning force is better described by a model incorporating an exponential decay term attributed to pronounced thermally-assisted flux flow. The Hall effect in the Bi-2212 films exhibits an extensive anomaly with a double sign change that may challenge existing theoretical explanations for this poorly understood phenomenon in copper-oxide superconductors.

I. INTRODUCTION

The investigation of high-temperature superconductivity in copper-oxide materials remains one of the most captivating subjects in condensed matter physics. One member of the family of these superconductors, the compound Bi₂Sr₂CaCu₂O_{8+ δ} (Bi-2212), stands out due to its weakly coupled layered structure that gives rise to the highest anisotropy in this class of materials. The unit cell of Bi-2212 is composed of two diagonally shifted subcells, each incorporating the nominal chemical formula. These distinctive features make it an exemplary system for exploring quasi-two-dimensional superconductivity.

Several studies on Bi-2212 single crystals have exploited their giant anisotropy [1-6], revealing novel observations such as the intrinsic Josephson effect along the c direction of the unit cell [7-9] and the modified version of the dc flux transformer geometry that confirmed that superconducting vortices are effectively two dimensional, commonly referred to as 'pancake vortices' [10, 11].

Experiments with thin Bi-2212 films, epitaxially grown on a suitable substrate, have enabled the realization of well-defined geometries but have been mainly limited to thicknesses of the superconducting layer of about 100 nm or more [12–17]. More recently, Bi-2212 whiskers and films with thicknesses of only a few unit cells attracted considerable interest for their enhancement of unconventional Hall effect [18], twisted van-der-Waals [19] and surface [20] Josephson junctions, and studies of the Nernst effect [21]. Remarkably, the most significant Nernst effect caused by the entropy transport of superconducting vortices was found in a 40-nm-thick Bi-2212 flake, surpassing the respective magnitudes in few-unit cell thin flakes and bulk materials [22]. While commercially available superconducting-nanowire single-photon detectors (SNSPDs) are based on metallic superconductors, initial success has been reported in implementing them with Bi-2212 thin films [23].

Few-unit-cell thick Bi-2212 whiskers and monolayers suffer from a major drawback—their instability under ambient conditions [24]. Maintaining their integrity requires sophisticated production processes in an inert gas atmosphere and meticulous handling during transfer to measurement systems [19, 22]. In contrast, previously investigated, about 100-nm-thin, Bi-2212 films are stable in dry air and can be handled conveniently. However, they are too thick for applications such as superconducting nanowire single-photon detectors and other experiments where penetration depth is a critical concern. Notably, it has recently been demonstrated that nanometric vortex-pinning landscapes [25-27] can be patterned with focused He-ion beams into thin $YBa_2Cu_3O_{7-\delta}$ (YBCO) films [28, 29]. Current studies are underway to extend this technique to thin Bi-2212 films, which must have a thickness of less than about 50 nm to allow full penetration of the employed 30 keV He^+ ions.

This study aims to provide valuable data on very thin Bi-2212 films by measurements of the anisotropic magnetoresistance with the magnetic field oriented perpendicular and parallel to the CuO_2 layers; the latter has been rarely explored so far. Critical current and Hall effect measurements provide additional insights into the transport properties of our samples. By presenting a detailed analysis of the electrical transport properties of Bi-2212 and providing estimates for the most important superconducting material parameters, we seek to contribute to the fundamental background to inspire future applications in electronic devices harnessing these remarkable materials.

^{*} These authors contributed equally to this work.

[†] Corresponding author: wolfgang.lang@univie.ac.at

II. MATERIALS AND METHODS

A. Fabrication of $Bi_2Sr_2CaCu_2O_{8+\delta}$ thin films

Pulsed-laser deposition (PLD) is the preferred method to fabricate high-quality thin films of Bi-2212 as described in more detail elsewhere [30]. Briefly, a substrate temperature of T = 780 °C and oxygen background pressure of $p(O_2) = 1.2$ mbar was used. Post-deposition *in-situ* annealing of the films at T = 600 °C ensured optimally-doped samples. Single-crystalline (0 0 1) LaAlO₃ (LAO) substrates with a lattice parameter $a_L =$ 3.82Å were used. The number of laser pulses (500 and 600 for films below 50 nm thickness) controls the film thickness, which was measured by atomic force microscopy (AFM) after UV-photolithographic structuring and wet-chemical etching.

The phase purity and orientation of the deposited films were analyzed via X-ray diffraction (XRD) with Cu K α radiation; θ -2 θ -scans were performed to verify the *c*-axis orientation of deposited films. The phase purity of the deposited Bi-2212 thin films, which can often suffer from the low- T_c phase ingrowth of Bi₂Sr₂CuO_y, was confirmed.

For the transmission electron microscopy (TEM) study, a 42-nm thin epitaxial Bi-2212 film was grown on $(\text{LaAlO}_3)_{0.3}(\text{Sr}_2\text{TaAlO}_6)_{0.7}$ (LSAT, $a_{\text{LSAT}} = 3.87$ Å) substrate and covered by a Pt-C protective layer before a focused gallium ion beam (Ga-FIB) was used to cut a thin lamella. Short imaging times of only a few minutes were used to not deteriorate the atomic structure, as longer times led to a complete amorphization of the film material.

For the electrical transport measurements, circular contact pads were established by evaporating Ag/Au pads (for optimal adhesion on the Bi-2212 film) through a copper shadow mask. Subsequently, the thin films with thicknesses 46 nm (42 nm) were patterned into rectangular-shaped bridges of $63 \,\mu\text{m}$ ($102 \,\mu\text{m}$) width and $94 \,\mu\text{m}$ ($497 \,\mu\text{m}$) distance between the voltage probes for sample A (sample B) by UV photolithography and wet chemical etching. Sample B was post-annealed in oxygen after patterning ($400 \,^\circ\text{C}$ for 30 min in 0.8 mbar oxygen atmosphere). Electrical contacts in the cryostat were established using silver paste and 50 μm thick gold wires.

B. Transport measurements

The sample's magnetoresistance R(T, B) as a function of temperature T and magnetic field B oriented perpendicular and parallel to the surface was measured in standard four-probe geometry in a physical properties measurement system (PPMS) using an external constant-current source (Keithley 6221) and a nanovoltmeter (Keithley 2182). The orientation of the magnetic field parallel to the *ab* direction of the Bi-2212 unit cell was adjusted by taking advantage of the sharp resistance minimum at the vortex lock-in [31] in an applied field at 9 T. For all orientations of the magnetic field, the transport current was perpendicular to the field. Measurements in zero or low magnetic fields were performed in a cryocooler placed between the pole pieces of an electromagnet.

The critical current was determined under isothermal and constant magnetic field conditions by increasing the current in small steps up to an electric field criterion of $10 \,\mu V/cm$ (corresponding to $100 \,nV$ for sample A and $500 \,nV$ for sample B) and interpolating between data points. Data at intense currents and low temperatures were excluded when the PPMS indicated a temperature rise due to sample heating by finite contact resistances. The Hall voltage V_y was collected during temperature sweeps at fixed magnetic fields in both polarities B^+ and B^- and calculated as $V_y = (V_{B^+} - V_{B^-})/2$. Occasional magnetic field sweeps confirmed the accuracy of this method.

III. RESULTS AND DISCUSSION

A. Superconducting transition and magnetoresistance

The epitaxial growth of our Bi-2212 films was checked on an identically prepared film by X-ray diffraction $\theta - 2\theta$ scans [see the inset of Fig. 1(a)]. The peaks could be allocated to the (0 0 *l*) reflections of Bi-2212, the LAO substrate, and the Al sample holder while no other phases have been detected. This also demonstrates the good *c*axis orientation of the unit cells grown on the crystalline substrate.

Cross-sectional TEM analysis confirmed the excellent epitaxial growth and layered structure of our thin Bi-2212 films. The half unit cell periodicity is clearly visible in Fig. 1(b), indicating that the 42-nm-thick Bi-2212 film consists of 13 unit cells stacked along the c direction. This number of layers corresponds to a calculation using the crystallographic unit cell parameters and the thickness of the film as determined by AFM.

The resistivities ρ_{xx} of the two samples are strictly linear from room temperature down to approximately 130 K, as shown in Fig. 1(a). This behavior is representative of optimally doped Bi-2212, whereas overdoped samples typically show a positive curvature and underdoped samples display a negative curvature in their $\rho_{xx}(T)$ curves [15]. Below 130 K, superconducting order parameter fluctuations introduce an additional paraconductivity contribution, causing $\rho_{xx}(T)$ to decrease as Tapproaches T_c [32]. The critical temperature $T_{c,inf}$, defined by the inflection point where $d^2\rho_{xx}/dT^2 = 0$ is $T_{c,inf} = 90.0 \text{ K}$ (sample A) and $T_{c,inf} = 88.0 \text{ K}$ (sample B). A linear extrapolation of the normal-state $\rho_{xx}(T)$ behavior to $\rho_{xx}(T) = 0$ yields slightly negative intercepts of about -30 K (sample A) and -20 K (sample B).

At room temperature, the resistivity $\rho_{xx}(300 \,\mathrm{K})$ closely



FIG. 1. (a) Resistivity of the two Bi-2212 samples in zero magnetic field. Inset: X-ray diffraction $\theta - 2\theta$ scans of another sample prepared identically. The asterisks mark peaks stemming from the aluminum sample holder. (b) Transmission electron micrograph of a 42 nm-thick Bi-2212 film revealing excellent epitaxial growth with only minor dislocations. The stripe-like features correspond to half-unit cell periodicity. The grey area at the top left is the LSAT substrate, and the black region at the bottom right is the Pt-C protection layer needed for lamella cutting.

matches that of optimally-doped Bi-2212 single crystals [33] and is only marginally higher than that reported for 200 nm thick Bi-2212 films [15]. This demonstrates that the substantial reduction in film thickness does not significantly increase the resistivity. Overall, these characteristics are consistent with those expected from high-quality, optimally doped copper-oxide superconductors.

In external magnetic fields applied perpendicular to the film surface—and thus orthogonal to the CuO_2 layers—the superconducting transitions broaden significantly, forming the characteristic 'fan-shape' commonly observed in copper-oxide superconductors. The inset of Fig. 2(a) illustrates this pronounced effect, consistent with earlier results obtained on 400 nm thick Bi-2212 films [13].

An Arrhenius plot of the magnetoresistivity, shown in Fig. 2(a), reveals linear behavior for $T \leq 91$ K, indicative of thermally-assisted flux flow (TAFF). In this regime, the resistivity can be described as

$$\rho_{\rm TAFF} \propto \exp\left(-U/k_{\rm B}T\right),$$
(1)

where U is the vortex pinning energy and $k_{\rm B}$ the Boltzmann constant. Independent tests at selected points confirmed that $\rho_{xx}(B,T)$ is ohmic up to currents an order of magnitude larger than those used in the main measurements. In zero magnetic field, however, the Arrhenius law no longer applies, and the curve acquires a negative curvature, presumably due to the absence of Abrikosov vortices. Notably, in our film, the Arrhenius relation holds perfectly over three decades of $\rho_{xx}(B,T)$, closely resembling the behavior reported in single-crystal experiments [34]. This contrasts earlier work on molecular-beam epitaxy (MBE) grown Bi-2212 films with 100 nm thickness, which exhibited a slight negative curvature and thus introduced uncertainties in determining the pinning energy U [35].

The magnetoresistivity is dramatically different when the magnetic field is oriented parallel to the CuO₂ planes, i.e., to the *ab* direction. A broadening of the superconducting transitions is barely detectable in magnetic fields up to 9 T [see the inset of Fig. 2(b)]. The Arrhenius law of Eq. (1) can be observed only for $\mu_0 H \gtrsim 0.3$ T while a negative curvature prevails at smaller magnetic fields, indicated by dashed lines in Fig. 2(b).

Furthermore, the pinning energy U shows a pronounced anisotropy, as illustrated in Fig. 3. Note that, due to the experimental geometry, a Lorentz force on vortices acts in both orientations of B. For $B \parallel c$, U is roughly twice as large as in Bi-2212 single crystals [11, 34] and follows a $B^{-1/2}$ dependence, suggesting that it is governed by the average lateral spacing of pancake vortices. This behavior differs markedly from the $U \propto 1/B$ trend commonly observed in thin films of less-anisotropic REBa₂Cu₃O_{7- δ} (RE-123, RE = rare earth element) superconductors [36], thereby underscoring the distinct vortex dynamics associated with Josephson-coupled pancake vortices in Bi-2212 compared to conventional Abrikosov vortices in RE-123.

For $B \parallel ab$, U is notably higher and exhibits only a weak dependence on B, as illustrated by the nonphysical relationship $B^{-1/9}$. This peculiar behavior presumably arises from the strong intrinsic pinning of Josephson vortices (JVs) by the stacked CuO₂ layers, effectively preventing JV hopping along the crystallographic c axis. Remarkably, at 1 T, the pinning energy in our film is almost



FIG. 2. Arrhenius plots of the magnetoresistivity of sample A under various magnetic fields. The solid lines are fits to Eq. (1), illustrating the thermally activated flux-flow regime. The dashed lines are guides to the eye. The insets present the respective data on linear scales. (a) Fields applied perpendicular to the CuO₂ planes. Data adapted from [30]. (b) Fields applied parallel to the CuO₂ planes. Note that all the curves nearly overlap in the inset.



FIG. 3. Vortex pinning energy $U/k_{\rm B}$, expressed in temperature units, determined from the fits to Eq. (1) using the data displayed in Fig. 2 (sample A). The lines represent power-law fits to the resulting U(B) dependencies.

an order of magnitude greater than that reported for Bi-2212 single crystals [34], and it decreases far more slowly as B increases. Given that the crystallographic quality of a single crystal should be at least comparable to that of an epitaxial thin film, we speculate that demagnetization effects could reduce the accuracy of measurements in crystals of finite thickness, especially when the precise alignment of the magnetic field vector is crucial.

The $\rho_{xx}(T, B)$ data of sample A, shown in Fig. 2, can be used to estimate the zero-temperature upper critical fields $B_{c2}^{\perp}(0)$ and $B_{c2}^{\parallel}(0)$ for B perpendicular and parallel to the CuO₂ layers, respectively. To this end, we define $B_{c2}(T)$ as the field at which $\rho_{xx}(T) = 0.5 \rho_{xx}(120 \text{ K})$. Subsequently, the Helfand-Werthamer relation for moderately dirty superconductors [37] is employed to extrapolate these critical fields to T = 0 K.

$$B_{c2}(0) \approx 0.7 T_{c} \frac{\mathrm{d}B_{c2}}{\mathrm{d}T} \Big|_{T_{c}}; B_{c2}(T) \ge 1 \mathrm{T}.$$
 (2)

The results for sample A are $B_{c2}^{\perp}(0) \approx 106 \,\mathrm{T}$ and $B_{c2}^{\parallel}(0) \approx 19,000 \,\mathrm{T}$, revealing an anisotropy parameter $\gamma = B_{c2}^{\parallel}(0)/B_{c2}^{\perp}(0) \approx 180$. For sample B we find $B_{c2}^{\perp}(0) \approx 86 \,\mathrm{T}$.

Using the Ginzburg-Landau relations

$$B_{c2}^{\perp}(0) = \frac{\Phi_0}{2\pi\xi_{ab}^2}$$
 and $B_{c2}^{\parallel}(0) = \frac{\Phi_0}{2\pi\xi_{ab}\xi_c}$ (3)

we obtain the zero-temperature Ginzburg-Landau coherence lengths $\xi_{ab} \approx 1.8 \,\mathrm{nm}$ and $\xi_c \approx 0.01 \,\mathrm{nm}$ in the inplane and out-of-plane directions for sample A, respectively, and $\xi_{ab} \approx 2.0 \,\mathrm{nm}$ for sample B. The extremely small ξ_c reflects the large anisotropy of Bi-2212 and is notably smaller than even in oxygen-depleted YBa₂Cu₃O_{6.6} [38].

An alternative method to estimate coherence lengths involves analyzing the paraconductivity and magnetoconductivity induced by superconducting order parameter fluctuations. Such studies in single crystals and thin films have reported ξ_{ab} values ranging from 0.9 nm to 3.8 nm and ξ_c between $\lesssim 0.04$ nm and 0.1 nm [39]. Our even smaller estimate for ξ_c confirms the excellent CuO₂layer stacking in our films and can be attributed to the careful alignment of the magnetic field with these layers.

B. Critical current

In the following, we consider thin films whose thickness t_z is much smaller than both their lateral dimensions and



FIG. 4. (a) Critical current density of sample A under self-field conditions. Inset: Same data plotted as a function of reduced temperature. The resulting linear relationship confirms the validity of Eq. (4). (b) Critical current density of sample B as a function of the external magnetic field at various temperatures. Inset: Semi-logarithmic plot of the data in the main panel. (c) Volume vortex pinning force of sample B as a function of the magnetic field at various temperatures. The solid lines represent fits to the power-law model as given by Eq. (6). (d) Normalized volume vortex pinning force of sample B. The solid lines represent fits to the exponential decay model of Eq. (7) with a fixed p = 0.9 and ε as plotted in Fig. 5(d). For comparison, the dashed line illustrates the behavior predicted by the power-law model [Eq. (6)] with the parameters p = 0.5 and q = 2.

the zero-temperature London penetration depths along the *ab* plane, λ_{ab} , and perpendicular, λ_c . Under these conditions, the superconducting current density J can be assumed to be homogeneous within the film. Fig. 4(a) presents the critical current density J_c^{sf} in the absence of an external magnetic field, i.e., in the current's self-field $B = \mu_0 J t_z/2$ [40]. The inset shows that the data conform well to the relation

$$J_{\rm c}^{\rm sf}(T) = J_{\rm c}^{\rm sf}(0) \left(1 - \frac{T}{T_{\rm c0}}\right)^{3/2},\tag{4}$$

where $J_c^{\rm sf}(0)$ is the critical current density at zero temperature and T_{c0} is a fit parameter associated with the temperature at which ρ_{xx} vanishes [see Fig. 1(a)]. Although Eq. (4) strictly applies only near T_{c0} [41], it provides a good description of our data down to 42 K for sample A. Extrapolating to T = 0 yields $J_{\rm sf}(0) \approx 10.3 \,\mathrm{MA/cm}^2$, which should be regarded as an upper limit. Of course, an accompanying estimate of the minimum $J_{\rm sf}(0)$ in our Bi-2212 films is also warranted. For this lower bound, measurements revealed $J_{\rm sf}(6\,{\rm K}) = 5.1\,{\rm MA/cm}^2$ in sample B, though this value is subject to some uncertainty due to heating from dissipation at the current contacts. Even so, any systematic temperature error would lead to an underestimate of $J_{\rm sf}(0)$, thereby reinforcing our conservative lower-limit estimate of $J_{\rm sf}(0) \ge 5.1\,{\rm MA/cm}^2$.

For thin microbridges with the above-mentioned geometrical constraints, it has been proposed [42, 43] that $J_{\rm sf}$ is determined by the lower critical field as $J_{\rm c}^{\rm sf} = H_{\rm cl}^{\perp}/\lambda_{ab}$, leading to an expression confirmed in many superconducting materials

$$J_{c}^{\rm sf}(0) = \frac{\Phi_{0}}{4\pi\mu_{0}\lambda_{ab}^{3}} \left(\ln\frac{\lambda_{ab}}{\xi_{ab}} + 0.5\right).$$
 (5)

By inserting the previously determined values $\xi_{ab} = 1.8 \,\mathrm{nm}$ for sample A and $\xi_{ab} = 2.0 \,\mathrm{nm}$ for sample B

into Eq. (5), we obtain an estimate for $\lambda_{ab} \gtrsim 190 \,\mathrm{nm}$ (sample A) and $\lambda_{ab} \lesssim 240 \,\mathrm{nm}$ (sample B). Furthermore, applying the mean-field temperature dependence $\lambda_{ab}(T) \propto (1 - T/T_c)^{-1/2}$ in Eq. (5) yields the temperature dependence shown in the inset of Fig. 4(a).

Now we focus on the critical current density of Bi-2212 films in a magnetic field applied parallel to the c axis. As previously observed [12, 44, 45], $J_c(B,T)$ decreases rapidly with increasing field strength. This trend is evident in Fig. 4(b), where the main panel presents $J_c(B)$ on a linear scale, and the inset shows the same data on a semi-logarithmic scale. For instance, at 45 K ~ $T_c/2$, J_c diminishes approximately one order of magnitude up to 1 T, following an almost exponential decay.

A direct comparison with data on other Bi-2212 films [44] can be made at 50 K. Our 42-nm film exhibits $J_{\rm c}^{\rm sf} = 1.6 \,{\rm MA/cm}^2$ and a ratio $J_{\rm c}^{\rm sf}/J_{\rm c}(1\,{\rm T}) \sim 100$, while a 100 nm film [44] shows $J_{\rm c}^{\rm sf} \simeq 0.06 \,{\rm MA/cm}^2$ and $J_{\rm c}^{\rm sf}/J_{\rm c}(1\,{\rm T}) \sim 200$. Additionally, another study on a 50-nm film [12] reported $J_{\rm c}^{\rm sf} = 1.0 \,{\rm MA/cm}^2$, about half of our sample A's value of $J_{\rm c}^{\rm sf}(50\,{\rm K}) = 2.2 \,{\rm MA/cm}^2$.

Surprisingly, Bi-2212 films containing self-assembled NiO nanorods exhibit a $J_c^{\rm sf}$ at ~ $T_c/2$ that is about two orders of magnitude lower than that of our samples. Nonetheless, despite the presence of these artificial pinning centers, the relative field-dependent decay $J_c(B)$ is very similar to our samples [45]. This suggests that our very thin Bi-2212 films provide significantly stronger intrinsic pinning than typically observed in single crystals [46] or even in most 100-nm thick films [44]. It is wellestablished that nanostrain can enhance vortex pinning in HTS [47]. In the case of these very thin films, the lattice mismatch with the LAO substrate likely cannot fully relax within the limited thickness. As a result, residual strain remains in the Bi-2212 layers, strengthening the pinning potential and yielding higher J_c values compared to thicker films.

The $J_{\rm c}(B,T)$ data can be further analyzed in terms of the volume pinning force $F_{\rm p}(B,T)$ by a well-established, semi-phenomenological scaling approach [48, 49] that is represented by the Kramer–Dew–Hughes model

$$F_{\rm p}(B,T) = J_{\rm c}(B,T)B = F_{\rm p}^* \left(\frac{B}{B^*}\right)^p \left(1 - \frac{B}{B^*}\right)^q.$$
 (6)

In metallic superconductors, B^* corresponds to B_{c2} . For HTS, however, it is more appropriately associated with the irreversibility field B_{irr} . F_p^* is a temperaturedependent scaling parameter, while the dimensionless exponents p and q reflect the specific nature and dimensionality of the pinning centers—whether they are point-like, linear, or planar defects.

In a simplified model, each vortex experiences a pinning force per unit length $f_{\rm p}$. At moderate fields, where vortices are sufficiently dilute, the volume pinning force can be approximated by $F_{\rm p} = \rho_A f_{\rm p}$, where ρ_A is the areal density of vortices. Since the inter-vortex spacing scales as $B^{1/2}$ and the number of vortices within a given volume



FIG. 5. Fit parameters obtained from the power-law and exponential decay models. (a) Magnetic field B^{peak} corresponding to the maximum in the volume pinning force, along with the magnetic field scaling parameter B^* . (b) Peak value of the volume vortex pinning force F_p^{peak} and its associated scaling parameter F_p^* . (c) Parameter q of Eq. (6). (d) Parameter ε of Eq. (7). The dashed lines represent a linear fit for F_p^* and a power-law fit for F_p^* . Dotted curves are guides to the eye.

scales with B, theoretical considerations suggest that p is in the range 0.5...10 [49]. At higher magnetic fields, collective vortex effects become more significant. It has been argued that, under these conditions, the second factor in Eq. (6) is dominated by the softening of the shear modulus c_{66} of the flux line lattice [48], which leads to a value q = 2.

Fig. 4(c) shows the field dependence of the volume pinning force $F_{\rm p}(B,T)$, which exhibits the characteristic shape commonly observed in HTS. In comparison to YBCO, the maximum pinning force $F_{\rm p}^{\rm max}$ in Bi-2212 thin films is notably smaller and occurs at approximately onetenth the magnetic field B. This shift and reduction are not unexpected, given the substantially weaker pinning of two-dimensional, pancake-like vortices in Bi-2212 and the absence of strong, micro-twin-boundary-induced pinning centers that are known to enhance $F_{\rm p}(B,T)$ in YBCO.

The temperature dependencies of the fit parameters B^* , F_p^* , and q are shown in Fig. 5. While the magnetic field associated with maximum pinning force, B^{peak} , decreases substantially as the temperature increases, the scaling parameter B^* exhibits only a minor dependence, as shown in Fig. 5(a). A similar pattern emerges in Fig. 5(b) for F_p^{peak} accompanied by a much weaker temperature dependence of F_p^* . The parameter $p = 0.57 \dots 0.68$ remains nearly constant with respect to temperature, indicating that point-like defects dominate the pinning mechanism. In contrast, q exhibits an unphysical deviation from the theoretically expected value of $q \sim 2$ once T > 45 K, as displayed in Fig. 5(c). This anomaly, combined with the unexpectedly weak temperature.

ture dependence of B^* , which should closely follow the irreversibility field $B_{\rm irr}$, suggests that the model in Eq. (6) may not be fully applicable to Bi-2212 thin films, despite the seemingly good fits presented in Fig. 4(c).

The exponential decrease of resistivity with inverse temperature, as depicted in Fig. 2(a), strongly suggests that an exponential decay model [50, 51] provides a more accurate representation of the observed data

$$F_{\rm p}(B,T) = F_{\rm p}^* \left(\frac{B}{B^*}\right)^p \exp\left(1 - \frac{B}{B^*}\right)^{\varepsilon} \frac{p}{\varepsilon}.$$
 (7)

By normalizing the data to the experimentally determined values $F_{\rm p}^{\rm peak}$ and $B^{\rm peak}$, the model effectively reduces to just two adjustable parameters. As demonstrated in Fig. 4(d), employing a fixed p = 0.9 and a parameter range $0.5 \le \varepsilon \le 1.5$ [see Fig. 5(d)] yields satisfactory agreement with the experimental data. This normalized representation also facilitates a more robust assessment of the fit quality across a wide range of temperatures. For comparison, the dashed line shows the prediction of the power-law model [Eq. (6)] with the parameters p = 0.5 and q = 2. Although the power-law model reproduces experimental results well up to B^{peak} , qualitative inspections indicate that it cannot capture the extended tails of $F_{\rm p}$ at $B \gg B^{\rm peak}$. A similar shortcoming was also observed in Bi-2223 thin films [52]. The inability of the power-law model to accurately describe the volume pinning force in Bi-2212 highlights the distinctive vortex dynamics in this material. Compared to YBCO and other less anisotropic superconductors, where power-law scaling has been successfully applied [53], Bi-2212 exhibits more complex behavior.

C. Hall effect

One of the most intriguing phenomena observed in HTS is their unconventional Hall effect, closely associated with the 'strange-metal' state observed predominantly in optimally doped HTS [54]. In our Bi-2212 thin films, this unconventional behavior is even more pronounced. Unlike conventional metals, where the Hall coefficient remains relatively constant with temperature and serves as a direct measure of carrier type and density, Fig. 6(a) demonstrates that the situation is considerably more complex in Bi-2212.

The Hall coefficient is defined as $R_{\rm H} = E_y/(j_x B_z)$, where E_y is the transverse electric field measured between the opposite side arms of the bridge, j_x the current density along the bridge, and B_z the magnetic field applied perpendicular to the film's surface. The positive sign of $R_{\rm H}$ confirms hole-like carriers as the dominant charge carriers. As the temperature decreases, $R_{\rm H}$ initially increases until a pronounced negative curvature sets in around 120 K, ultimately giving way to a sharp drop at $T_c(B)$. These features can be attributed to a negative contribution from superconducting orderparameter fluctuations [55], underscoring the intricate interplay between the normal-state and superconducting regimes in these materials.

The carrier mobility inferred from the Hall effect $\mu_{\rm H} = \tan \theta_{\rm H}/B_z = R_{\rm H}/\rho_{xx}$, where $\tan \theta_{\rm H} = E_y/E_x$ is the Hall angle, decreases with increasing temperature. A characteristic yet unconventional trend commonly observed in HTS is $\cot \theta_{\rm H} = \alpha T^2 + C$, where C is proportional to the density of carrier-scattering defects, and α relates to the inverse carrier density [56]. As shown in Fig. 7, this relationship also holds for our Bi-2212 films. Extrapolation of the data to $T^2 = 0$ gives $\cot \theta_{\rm H}(1T, 0 \,{\rm K}) = 0.06$ whereas in 100 nm to 200 nmthick films $\cot \theta_{\rm H}(1\,{\rm T},0\,{\rm K}) = 0.01$ has been reported [16]. We attribute our higher value to an increased density of scattering defects, possibly arising from lattice mismatch at the substrate interface. Such defects, which cannot fully relax in ultra-thin films, may create stacking faults that lead to stronger vortex pinning and thus explain the exceptionally high critical currents observed in our samples.

While $R_{\rm H}$ in the normal state is field-independent (at least up to 9 T), it becomes strongly *B*-dependent near and below the superconducting transition. Most remarkably, a sign change of $R_{\rm H}$ occurs in the vortex-liquid regime as displayed in Fig. 6(a). It was initially reported in YBCO [57] and BSCCO ceramics [58] and is now recognized as a general feature of HTS, irrespective of their morphology. Various theories have been proposed to explain this Hall anomaly, including renormalized superconducting fluctuations [55], collective vortex effects [59], and the role of pinning centers [60]. Still, a consensus has not yet emerged [18, 61].

The amplitude of the negative $R_{\rm H}$ peak decreases markedly with increasing B_z , and by $B_z \ge 6 \,\mathrm{T}$, the sign change disappears. Still, a minor dip remains visible in the inset of Fig. 6(a). Most remarkably, at $B_z = 0.5 \,\mathrm{T}$, the negative Hall signal surpasses even the maximum positive $R_{\rm H}$ observed in the normal state. This effect is far more pronounced in our very thin Bi-2212 films than reported elsewhere, potentially challenging existing theoretical models of the Hall anomaly.

To properly interpret these results, it is important to consider the magneto-conductivity tensor. The measured quantities ρ_{xx} and $\rho_{yx} = R_{\rm H}B_z$ relate to their conductivity counterparts via tensor inversion: $\rho_{xx} = \sigma_{xx}/(\sigma_{xx}^2 + \sigma_{xy}^2)$ and $\rho_{yx} = \sigma_{xy}/(\sigma_{xx}^2 + \sigma_{xy}^2)$. In the materials and magnetic fields under investigation $\sigma_{xx} \gg \sigma_{xy}$. Thus, $\rho_{xx} \simeq \sigma_{xx}^{-1}$ and $\rho_{yx} \simeq \sigma_{xy}/\sigma_{xx}^2$. Even if σ_{xy} in the vortex-liquid regime is believed to be largely unaffected by pinning [62], the observable $R_{\rm H}$ depends strongly on it [55].

It is illustrative to discuss a renormalized quantity, σ_{xy}/B , presented in Fig. 6(b). In the normal state, $\sigma_{xy}/B \propto T^{-2}$. Just above T_c a sharp negative trend emerges, producing dramatically larger negative values of σ_{xy}/B than any positive values observed in the normal state for $B \leq 2 \text{ T}$ [see the inset in Fig. 6(b)]. A possible explanation of this effect and a quantitative model of



FIG. 6. (a) Hall coefficient measured in multiple magnetic fields applied perpendicular to the *ab* planes of the Bi-2212 thin film (sample B). The inset provides a magnified view to emphasize the sign reversal of the Hall effect. (b) Renormalized Hall conductivity σ_{xy}/B as a function of temperature under various magnetic fields. The gray dashed line illustrates a T^{-2} dependence of the normal-state σ_{xy}/B . Inset: Detailed view of the Hall effect sign change.



FIG. 7. Reciprocal tangent of the Hall angle plotted as a function of the squared temperature (Sample B).

the shape of the respective $R_{\rm H}(B,T)$ curves has been presented elsewhere [55]. The model is based on superconducting order-parameter fluctuations and a lowtemperature cutoff by a diverging σ_{xx} due to pinning.

However, in Bi-2212 another twist occurs: at 4 T, we observe a second sign reversal back to positive σ_{xy}/B . The effect may also exist in a broader *B* range, but at lower fields, the Hall signal falls below the measurement resolution, and at higher fields, a residual dip, too weak to induce a sign reversal, is still detectable. Such a double sign change is notably pronounced in few-unit-cell Bi-2212 whiskers [18], and we also see it in our approximately 13-unit-cell-thick films at similar temperatures.

Some observations in YBCO thin films hint that this second sign change may be related to pinning. In low fields, where intrinsic pinning is strong, a second sign reversal emerges in YBCO [63]. Furthermore, YBCO samples patterned with a periodic pinning array via masked ion irradiation also exhibit a second Hall sign reversal [64]. More studies are required to clarify the origin of this phenomenon in Bi-2212, and very thin films, as reported here, could be an excellent material for this endeavor.

Finally, Table I summarizes the parameters obtained from our various measurements. Despite apparent differences between fabrication of the two samples, the fundamental superconducting parameters, including the upper critical field $B_{c2}^{ab}(0)$, in-plane coherence length ξ_{ab} , London penetration depth λ_{L}^{ab} , and the Ginzburg-Landau parameter κ , differ by no more than about 30%. This consistency underscores the reproducibility of our results and provides a solid foundation for future studies on the properties of few-unit-cell thin Bi-2212 films.

IV. CONCLUSIONS

Investigations of Bi-2212 films of about 13 unit cell thickness on LaAlO₃ substrates demonstrate a significantly enhanced critical current density. This improvement is likely attributable to strain-induced effects from the substrate, which reinforce vortex pinning. Unlike YBCO, the volume pinning force in these films does not follow the conventional Kramer–Dew–Hughes model but is instead well-described by an exponential decay.

Magnetoresistance measurements with fields applied perpendicular and parallel to the CuO_2 layers reveal thermally assisted flux flow behavior in the perpendicular configuration and evidence of stronger vortex pinning in parallel fields. From these data, we determine an anisotropy of around 180, as well as the in-plane and out-of-plane Ginzburg-Landau coherence lengths and the London penetration depth.

TABLE I. Summary of the superconducting parameters of very thin Bi-2212 films obtained in this study; Critical temperature T_c , upper critical fields with B oriented perpendicular and parallel to the CuO₂ layers, $B_{c2}^{\perp}(0)$ and $B_{c2}^{\parallel}(0)$, in-plane and out-of-plane Ginzburg-Landau coherence lengths at zero temperature ξ_{ab} and ξ_c , self-field critical current at 45 K $J_c^{sf}(45 \text{ K})$, in-plane London penetration depth at zero temperature λ_{ab} , anisotropy parameter γ , and Ginzburg-Landau parameter κ . The uncertainties in the evaluation of these parameters are discussed in the text.

	$T_{\rm c}$	$B_{\mathrm{c2}}^{\perp}(0)$	$B_{\mathrm{c2}}^{\parallel}(0)$	ξ_{ab}	ξ_c	$J_{\rm c}^{\rm sf}(45{\rm K})$	λ_{ab}	γ	κ
	(K)	(T)	(T)	(nm)	(nm)	(MA/cm^2)	(nm)		
Sample A	90	106	19,000	1.8	0.01	2.89	$\gtrsim 190$	180	$\gtrsim 106$
Sample B	88	86	-	2.0	_	2.20	$\lesssim 240$	_	$\lesssim 120$

The Hall effect follows the typical temperature dependence of optimally-doped HTS in the normal state, yet exhibits a remarkably pronounced anomaly. Within a certain magnetic field range, the Hall signal undergoes two sign reversals, a feature that is even more pronounced here than in ultrathin Bi-2212 whiskers. This makes our films a compelling model system for further investigations into this poorly understood phenomenon in HTS.

Finally, the stability of these very thin Bi-2212 films under ambient conditions offers clear advantages over few-unit-cell-thick whiskers, which are more environmentally sensitive. Still, such films are sufficiently thin to harness their advantages over conventional thicker films, such as complete ion and photon penetration at moderate energies and high critical currents, paving the way for novel quantum devices.

- A. Samoilov, Universal behavior of the Hall resistivity of single crystalline Bi₂Sr₂CaCu₂O_x in the thermally activated flux flow regime, Phys. Rev. Lett. **71**, 617 (1993).
- [2] Y. Latyshev, O. Laborde, and P. Monceau, The normalstate magnetoresistance of BSCCO 2:2:1:2 single-crystal whiskers, Europhysics Letters 29, 495 (1995).
- [3] G. Heine, W. Lang, X. L. Wang, and S. X. Dou, Positive in-plane and negative out-of-plane magnetoresistance in the overdoped high-temperature superconductor Bi₂Sr₂CaCu₂O_{8+x}, Phys. Rev. B **59**, 11179 (1999).
- [4] X. L. Wang, H. K. Liu, S. X. Dou, J. Horvat, D. Millikon, G. Heine, W. Lang, H. M. Luo, and S. Y. Ding, Superconductivity and flux pinning in Y and heavily Pb codoped Bi-2212 single crystals, J. Appl. Phys. 89, 7669 (2001).
- [5] S. Bending, D. Cole, S. Savel'ev, F. Nori, and T. Tamegai, Ratchet without spatial asymmetry: Controlling the motion of magnetic flux quanta using time-asymmetric drives, Physica C 460-462, 1266 (2007).
- [6] R. Ogawa, F. Nabeshima, T. Nishizaki, and A. Maeda, Large Hall angle of vortex motion in high- T_c cuprate superconductors revealed by microwave flux-flow Hall effect, Phys. Rev. B **104**, 10.1103/PhysRevB.104.L020503 (2021).
- [7] R. Kleiner, F. Steinmeyer, G. Kunkel, and P. Müller, Intrinsic Josephson effects in Bi₂Sr₂CaCu₂O₈ single crystals, Phys. Rev. Lett. 68, 2394 (1992).

ACKNOWLEDGMENTS

This research was funded in whole, or in part, by the Austrian Science Fund (FWF) grant number I4865-N. For the purpose of open access, the authors have applied a CC BY public copyright license to any Author Accepted Manuscript version arising from this submission. B.A. acknowledges financial support from the Austrian Science Fund, grant I6079. This article is based upon work from COST Actions SuperQuMap CA21144, Hi-SCALE CA19108, and Polytopo CA23134 (European Cooperation in Science and Technology).

- [8] L. Ozyuzer, A. E. Koshelev, C. Kurter, N. Gopalsami, Q. Li, M. Tachiki, K. Kadowaki, T. Yamamoto, H. Minami, H. Yamaguchi, T. Tachiki, K. E. Gray, W.-K. Kwok, and U. Welp, Emission of Coherent THz Radiation from Superconductors, Science **318**, 1291 (2007).
- [9] R. Kleiner, X. Zhou, E. Dorsch, X. Zhang, D. Koelle, and D. Jin, Space-time crystalline order of a high-criticaltemperature superconductor with intrinsic Josephson junctions, Nat. Commun. 12, 6038 (2021).
- [10] H. Safar, E. Rodriguez, F. de la Cruz, P. L. Gammel, L. F. Schneemeyer, and D. J. Bishop, Observation of twodimensional vortices in Bi₂Sr₂CaCu₂O_x, Phys. Rev. B 46, 14238 (1992).
- [11] R. Busch, G. Ries, H. Werthner, G. Kreiselmeyer, and G. Saemann-Ischenko, New aspects of the mixed state from 6-terminal measurements on $Bi_2Sr_2CaCu_2O_x$ single crystals, Phys. Rev. Lett. **69**, 522 (1992).
- [12] P. Schmitt, L. Schultz, and G. Saemann-Ischenko, Electrical properties of $Bi_2Sr_2CaCu_2O_x$ thin films prepared in situ by pulsed laser deposition, Physica C 168, 475 (1990).
- [13] H. C. Ri, R. Gross, F. Gollnik, A. Beck, R. P. Huebener, P. Wagner, and H. Adrian, Nernst, Seebeck, and Hall effects in the mixed state of $YBa_2Cu_3O_{7-\delta}$ and $Bi_2Sr_2CaCu_2O_{8+x}$ thin films a comparative study, Phys. Rev. B **50**, 3312 (1994).
- [14] Z. Konstantinovic, O. Laborde, P. Monceau, Z. Z.

Li, and H. Raffy, Normal state magnetoresistance in $Bi_2Sr_2CaCu_2O_{8+\delta}$ thin films with different oxygen contents, Physica B **259-261**, 569 (1999).

- [15] Z. Konstantinovic, Z. Z. Li, and H. Raffy, Temperature dependence of the resistivity of oxygen controlled Bi₂Sr₂CaCu₂O_{8+ δ} thin films: pseudogap effect, Physica B **259**, 567 (1999).
- [16] Z. Konstantinovic, Z. Z. Li, and H. Raffy, Temperature dependence of the Hall effect in single-layer and bilayer $Bi_2Sr_2Ca_{n-1}Cu_nO_y$ thin films at various oxygen contents, Phys. Rev. B **62**, R11989 (2000).
- [17] R. Rössler, J. D. Pedarnig, and C. Jooss, Bi₂Sr₂Ca_{n-1}Cu_nO_{2(n+2)+ δ} thin films on *c*-axis oriented and vicinal substrates, Physica C **361**, 13 (2001).
- [18] S. Y. F. Zhao, N. Poccia, M. G. Panetta, C. Yu, J. W. Johnson, H. Yoo, R. Zhong, G. D. Gu, K. Watanabe, T. Taniguchi, S. V. Postolova, V. M. Vinokur, and P. Kim, Sign-reversing Hall effect in atomically thin high-temperature Bi_{2.1}Sr_{1.9}CaCu_{2.0}O_{8+δ} superconductors, Phys. Rev. Lett. **122**, 247001 (2019).
- [19] S. Y. F. Zhao, X. Cui, P. A. Volkov, H. Yoo, S. Lee, J. A. Gardener, A. J. Akey, R. Engelke, Y. Ronen, R. Zhong, G. Gu, S. Plugge, T. Tummuru, M. Kim, M. Franz, J. H. Pixley, N. Poccia, and P. Kim, Time-reversal symmetry breaking superconductivity between twisted cuprate superconductors, Science **382**, 1422 (2023).
- [20] Z. Wei, H. Du, D. Li, M. P. Jiang, P. Zhang, S. Chen, Y.-Y. Lyu, H. Sun, Y.-L. Wang, D. Koelle, R. Kleiner, H. Wang, and P. Wu, Tailoring Bi₂Sr₂CaCu₂O_{8+δ} surface Josephson junctions, Appl. Phys. Lett. **122**, 112601 (2023).
- [21] S. Hu, J. Qiao, G. Gu, Q.-K. Xue, and D. Zhang, Vortex entropy and superconducting fluctuations in ultrathin underdoped Bi₂Sr₂CaCu₂O_{8+x} superconductor, Nat. Commun. 15, 4818 (2024).
- [22] S. Shokri, M. Ceccardi, T. Confalone, C. N. Saggau, Y. Lee, M. Martini, G. Gu, V. M. Vinokur, I. Pallecchi, K. Nielsch, F. Caglieris, and N. Poccia, Evolution of dissipative regimes in atomically thin Bi₂Sr₂CaCu₂O_{8+x} superconductor, Adv. Electron. Mater. **2024**, 2400496 (2024).
- [23] I. Charaev, D. A. Bandurin, A. T. Bollinger, I. Y. Phinney, I. Drozdov, M. Colangelo, B. A. Butters, T. Taniguchi, K. Watanabe, X. He, O. Medeiros, I. Božović, P. Jarillo-Herrero, and K. K. Berggren, Singlephoton detection using high-temperature superconductors, Nat. Nanotechnol. 18, 343 (2023).
- [24] Y. Yu, L. Ma, P. Cai, R. Zhong, C. Ye, J. Shen, G. D. Gu, X. H. Chen, and Y. Zhang, High-temperature superconductivity in monolayer $\text{Bi}_2\text{Sr}_2\text{CaCu}_2\text{O}_{8+\delta}$, Nature **575**, 156 (2019).
- [25] W. Lang, H. Richter, M. Marksteiner, K. Siraj, M. A. Bodea, J. D. Pedarnig, C. Grigoropoulos, D. Bäuerle, C. Hasenfuss, L. Palmetshofer, R. Kolarova, and P. Bauer, Masked ion beam irradiation of hightemperature superconductors: patterning of nano-size regions with high point-defect density, Int. J. Nanotechnol. 6, 704 (2009).
- [26] J. D. Pedarnig, K. Siraj, M. A. Bodea, I. Puica, W. Lang, R. Kolarova, P. Bauer, K. Haselgrübler, C. Hasenfuss, I. Beinik, and C. Teichert, Surface planarization and masked ion-beam structuring of YBa₂Cu₃O₇ thin films, Thin Solid Films **518**, 7075 (2010).
- [27] L. T. Haag, G. Zechner, W. Lang, M. Dosmailov, M. A.

Bodea, and J. D. Pedarnig, Strong vortex matching effects in YBCO films with periodic modulations of the superconducting order parameter fabricated by masked ion irradiation, Physica C **503**, 75 (2014).

- [28] B. Aichner, B. Müller, M. Karrer, V. R. Misko, F. Limberger, K. L. Mletschnig, M. Dosmailov, J. D. Pedarnig, F. Nori, R. Kleiner, D. Koelle, and W. Lang, Ultradense tailored vortex pinning arrays in superconducting YBa₂Cu₃O_{7- δ} thin films created by focused He ion beam irradiation for fluxonics applications, ACS Appl. Nano Mater. **2**, 5108 (2019).
- [29] M. Karrer, B. Aichner, K. Wurster, C. Magén, C. Schmid, R. Hutt, B. Budinská, O. V. Dobrovolskiy, R. Kleiner, W. Lang, E. Goldobin, and D. Koelle, Vortex matching at 6 T in YBa₂Cu₃O_{7-δ} thin films by imprinting a 20-nm periodic pinning array with a focused helium-ion beam, Phys. Rev. Applied **22**, 014043 (2024).
- [30] S. Keppert, B. Aichner, R. Adhikari, B. Faina, W. Lang, and J. D. Pedarnig, Phase purity and surface morphology of high- J_c superconducting Bi₂Sr₂Ca₁Cu₂O_{8+ δ} thin films, Appl. Surf. Sci. **636**, 157822 (2023).
- [31] M. Tachiki and S. Takahashi, Strong vortex pinning intrinsic in high-T_c oxide superconductors, Solid State Commun. **70**, 291 (1989).
- [32] A. Larkin and A. Varlamov, *Theory of fluctuations in superconductors* (Clarendon Press, Oxford, 2005).
- [33] T. Watanabe, T. Fujii, and A. Matsuda, Anisotropic resistivities of precisely oxygen controlled single-crystal Bi₂Sr₂CaCu₂O_{8+δ}: Systematic study on "spin gap" effect, Phys. Rev. Lett. **79**, 2113 (1997).
- [34] T. Palstra, B. Batlogg, L. Schneemeyer, and J. Waszczak, Thermally activated dissipation in $Bi_{2.2}Sr_2Ca_{0.8}Cu_2O_{8+\delta}$, Phys. Rev. Lett. **61**, 1662 (1988).
- [35] J. T. Kucera, T. P. Orlando, G. Virshup, and J. N. Eckstein, Magnetic-field and temperature dependence of the thermally activated dissipation in thin films of Bi₂Sr₂CaCu₂O_{8+δ}, Phys. Rev. B 46, 11004 (1992).
- [36] J. Z. Sun, K. Char, M. R. Hahn, T. H. Geballe, and A. Kapitulnik, Magnetic flux motion and its influence on transport properties of the high T_c oxide superconductors, Appl. Phys. Lett. 54, 663 (1989).
- [37] E. Helfand and N. R. Werthamer, Temperature and purity dependence of the superconducting critical field, H_{c2}. II, Phys. Rev. 147, 288 (1966).
- [38] W. Göb, W. Lang, W. Markowitsch, V. Schlosser, W. Kula, and R. Sobolewski, Erasable photoinduced change of carrier density and coherence lengths in oxygen-deficient YBa₂Cu₃O_x, Solid State Commun. 96, 431 (1995).
- [39] A. Pomar, M. V. Ramallo, J. Mosqueira, C. Torrón, and F. Vidal, Fluctuation-induced in-plane conductivity, magnetoconductivity, and diamagnetism of Bi₂Sr₂CaCu₂O₈ single crystals in weak magnetic fields, Phys. Rev. B 54, 7470 (1996).
- [40] A. A. Babaei Brojeny and J. R. Clem, Self-field effects upon the critical current density of flat superconducting strips, Supercond. Sci. Technol. 18, 888 (2005).
- [41] M. Y. Kupryanov and V. F. Lukichev, Temperature dependence of pair-breaking current in superconductors, Sov. J. Low Temp. Phys. (Engl. Transl.) 6, 210 (1980).
- [42] E. F. Talantsev and J. L. Tallon, Universal self-field critical current for thin-film superconductors, Nat. Commun. 6, 7820 (2015).

- [43] E. Talantsev, W. P. Crump, and J. L. Tallon, Thermodynamic parameters of single- or multi-band superconductors derived from self-field critical currents, Ann. Phys. 529, 1700197 (2017).
- [44] S. Labdi, H. Raffy, O. Laborde, and P. Monceau, Angular dependence of critical currents in Bi₂Sr₂CaCu₂O₈ thin films predominant role of the transverse magnetic field component, Physica C 197, 274 (1992).
- [45] X. Zhao, H. Tian, Y. Qi, X. Lu, Y. Ma, H. Li, J. Xiang, D. Ma, F. Wu, and T. Wang, A novel method to enhance the superconducting properties of $\text{Bi}_2\text{Sr}_2\text{CaCu}_2O_{8+\delta}$ superconducting thin films by self-assembly NiO nanorods, Ceram. Int. **50**, 35388 (2024).
- [46] J. van den Berg, C. J. van der Beek, P. H. Kes, J. A. Mydosh, M. J. V. Menken, and A. A. Menovsky, Critical current densities and the effects of thermally assisted flux flow in single crystals of Bi₂Sr₂CaCu₂O₈, Supercond. Sci. Technol. 1, 249 (1989).
- [47] Z. Li, M. Coll, B. Mundet, N. Chamorro, F. Vallès, A. Palau, J. Gazquez, S. Ricart, T. Puig, and X. Obradors, Control of nanostructure and pinning properties in solution deposited YBa₂Cu₃O_{7-x} nanocomposites with preformed perovskite nanoparticles, Sci. Rep. 9, 5828 (2019).
- [48] E. J. Kramer, Scaling laws for flux pinning in hard superconductors, J. Appl. Phys. 44, 1360 (1973).
- [49] D. Dew-Hughes, Flux pinning mechanisms in type II superconductors, Philos. Mag. 30, 293 (1974).
- [50] P. Fabbricatore, C. Priano, A. Sciutti, G. Gemme, R. Musenich, R. Parodi, F. Gömöry, and J. R. Thompson, Flux pinning in Bi-2212/Ag-based wires and coils, Phys. Rev. B 54, 12543 (1996).
- [51] M. Jirsa, M. R. Koblischka, T. Higuchi, M. Muralidhar, and M. Murakami, Comparison of different approaches to modelling the fishtail shape in RE-123 bulk superconductors, Physica C 338, 235 (2000).
- [52] H. Yamasaki, K. Endo, S. Kosaka, M. Umeda, S. Yoshida, and K. Kajimura, Scaling of the flux pinning force in epitaxial $Bi_2Sr_2Ca_2Cu_3O_x$ thin films, Phys. Rev. Lett. **70**, 3331 (1993).

- [53] E. F. Talantsev, New scaling laws for pinning force density in superconductors, Condens. Matter 7, 74 (2022).
- [54] N. Barišić and D. K. Sunko, High- T_c cuprates: a story of two electronic subsystems, J. Supercond. Nov. Magn. **35**, 1781 (2022).
- [55] I. Puica, W. Lang, W. Göb, and R. Sobolewski, Halleffect anomaly near T_c and renormalized superconducting fluctuations in YBa₂Cu₃O_{7-x}, Phys. Rev. B **69**, 104513 (2004), and references therein.
- [56] P. W. Anderson, Hall effect in the two-dimensional Luttinger liquid, Phys. Rev. Lett. 67, 2092 (1991).
- [57] M. Galffy and E. Zirngiebl, Hall-effect of bulk $YBa_2Cu_3O_{7-\delta}$, Solid State Commun. **68**, 929 (1988).
- [58] M. Galffy, Hall-effect of Bi-Sr-Ca-Cu-O, Solid State Commun. 72, 589 (1989).
- [59] P. Ao, Motion of vacancies in a pinned vortex lattice: origin of the Hall anomaly, J. Phys.: Condens. Matter 10, L677 (1998).
- [60] N. B. Kopnin and V. M. Vinokur, Effects of pinning on the flux flow Hall resistivity, Phys. Rev. Lett. 83, 4864 (1999).
- [61] R. Guo, Y.-C. Chen, and P. Ao, Hall anomaly by vacancies in a pinned lattice of vortices: A quantitative analysis based on the thin-film data from $Bi_{2.1}Sr_{1.9}CaCu_{2.0}O_{8+\delta}$, Phys. Rev. B **106**, 104507 (2022).
- [62] V. M. Vinokur, V. B. Geshkenbein, M. V. Feigel'man, and G. Blatter, Scaling of the Hall resistivity in high-T_c superconductors, Phys. Rev. Lett. **71**, 1242 (1993).
- [63] W. Göb, W. Liebich, W. Lang, I. Puica, R. Sobolewski, R. Rössler, J. D. Pedarnig, and D. Bäuerle, Double sign reversal of the vortex Hall effect in YBa₂Cu₃O_{7- δ} thin films in the strong pinning limit of low magnetic fields, Phys. Rev. B **62**, 9780 (2000).
- [64] G. Zechner, W. Lang, M. Dosmailov, M. A. Bodea, and J. D. Pedarnig, Transverse vortex commensurability effect and sign change of the Hall voltage in superconducting YBa₂Cu₃O_{7- δ} thin films with a nanoscale periodic pinning landscape, Phys. Rev. B **98**, 104508 (2018).